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Kind regards,

Team Nexperia



PIMC31

500 mA, 50 V NPN/PNP double resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

Rev. 01 — 24 March 2009

Product data sheet

1. Product profile

1.1 General description

500 mA, 50 V NPN/PNP double Resistor-Equipped Transistor (RET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PIMN31

1.2 Features

- 500 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital application in automotive and industrial segments
- Switching loads

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor; for the PNP transisto	or with negative polarity				
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	500	mA
R1	bias resistor 1 (input)		0.7	1	1.3	kΩ
R2/R1	bias resistor ratio		9	10	11	



500 mA, 50 V NPN/PNP double RET; R1 = 1 k Ω , R2 = 10 k Ω

2. Pinning information

Table 2. Pinning

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	[6 [5 [4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2	1 2 3	R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1		R2 R1 R1 1 2 3
			006aaa143

3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PIMC31	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

4. Marking

Table 4. Marking codes

Type number	Marking code
PIMC31	ZH

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

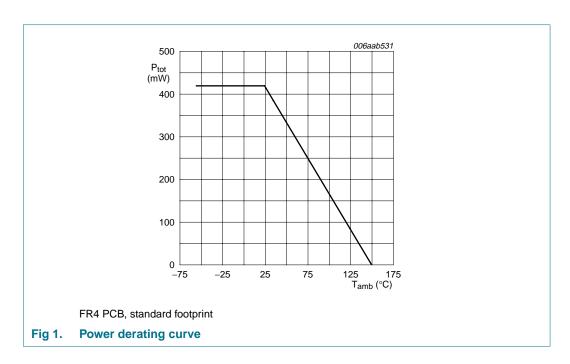
Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor	with negative polarity			
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
VI	input voltage TR1				
	positive		-	+10	V
	negative		-	- 5	V
	input voltage TR2				
	positive		-	+5	V
	negative		-	-10	V

500 mA, 50 V NPN/PNP double RET; R1 = 1 k Ω , R2 = 10 k Ω

Table 5. Limiting values ...continued In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I_{O}	output current		-	500	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	290	mW
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	420	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



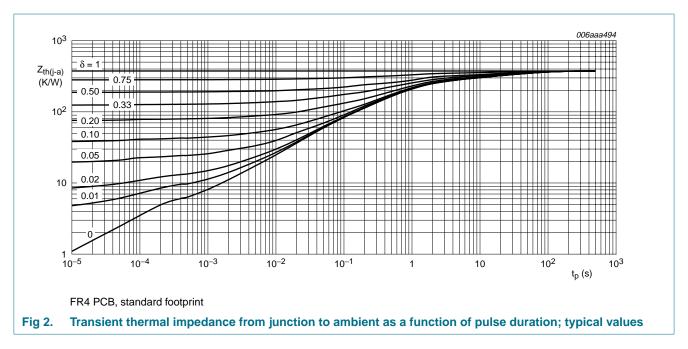
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	tor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	431	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	105	K/W
Per device						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	298	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

500 mA, 50 V NPN/PNP double RET; R1 = 1 k Ω , R2 = 10 k Ω



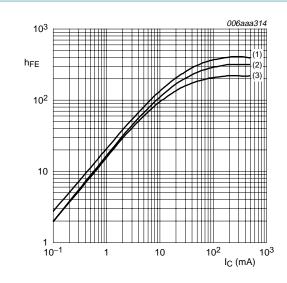
7. Characteristics

Table 7. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor; for the PNP transi	stor with negative polarity				
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 50 \text{ V}; I_{B} = 0 \text{ A}$	-	-	0.5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	0.72	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 50 \text{ mA}$	70	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 2.5 \text{ mA}$	-	-	0.3	V
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	0.3	0.6	1	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$	0.4	0.8	1.4	V
R1	bias resistor 1 (input)		0.7	1	1.3	kΩ
R2/R1	bias resistor ratio		9	10	11	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz				
	TR1 (NPN)		-	7	-	pF
	TR2 (PNP)		-	11	-	pF

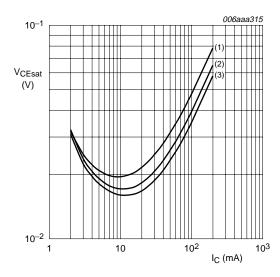
500 mA, 50 V NPN/PNP double RET; R1 = 1 k Ω , R2 = 10 k Ω



$$V_{CE} = 5 V$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

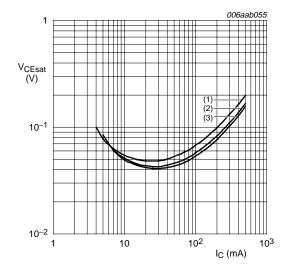
Fig 3. TR1 (NPN): DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values

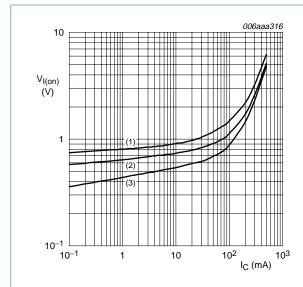


$$I_{\rm C}/I_{\rm B}=50$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 5. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values

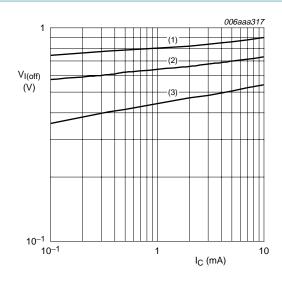
500 mA, 50 V NPN/PNP double RET; R1 = 1 k Ω , R2 = 10 k Ω



$$V_{CE} = 0.3 V$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. TR1 (NPN): On-state input voltage as a function of collector current; typical values

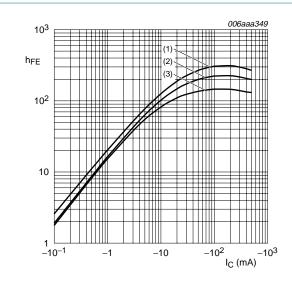


$$V_{CE} = 5 V$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. TR1 (NPN): Off-state input voltage as a function of collector current; typical values

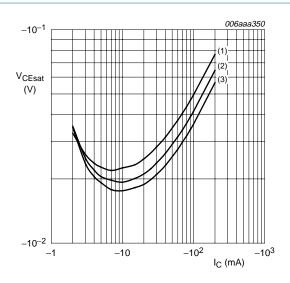
500 mA, 50 V NPN/PNP double RET; R1 = 1 k Ω , R2 = 10 k Ω



$$V_{CE} = -5 \text{ V}$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

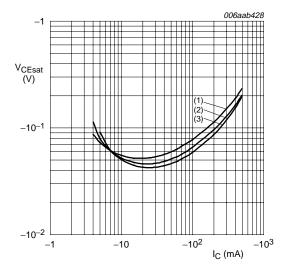
Fig 8. TR2 (PNP): DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 9. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

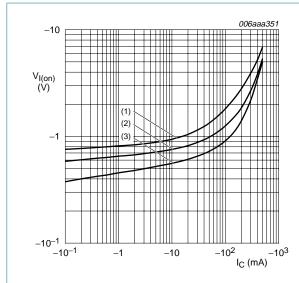


$$I_{\rm C}/I_{\rm B}=50$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

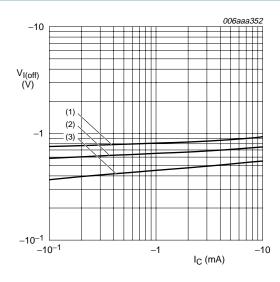
500 mA, 50 V NPN/PNP double RET; R1 = 1 k Ω , R2 = 10 k Ω



$$V_{CE} = -0.3 \text{ V}$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 11. TR2 (PNP): On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

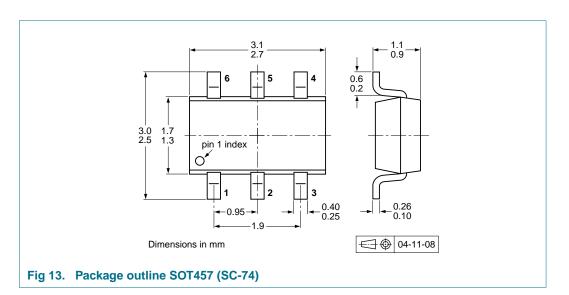
500 mA, 50 V NPN/PNP double RET; R1 = 1 k Ω , R2 = 10 k Ω

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description Pa		Packing quantity	
				3000	10000
		4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

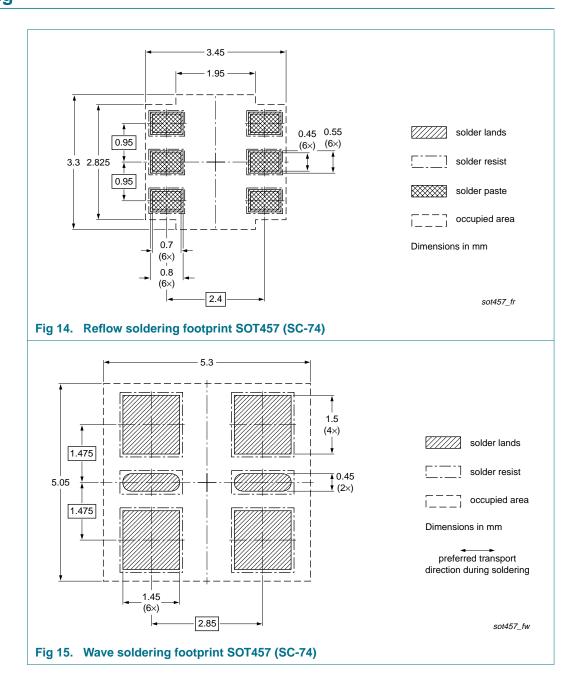
^[1] For further information and the availability of packing methods, see Section 14.

[2] T1: normal taping

[3] T2: reverse taping

500 mA, 50 V NPN/PNP double RET; R1 = 1 k Ω , R2 = 10 k Ω

11. Soldering



500 mA, 50 V NPN/PNP double RET; R1 = 1 kΩ, R2 = 10 kΩ

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PIMC31_1	20090324	Product data sheet	-	-

500 mA, 50 V NPN/PNP double RET; R1 = 1 k Ω , R2 = 10 k Ω

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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500 mA, 50 V NPN/PNP double RET; R1 = 1 k Ω , R2 = 10 k Ω

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